

Session Program

Dec 2 - 4, 2015

27th RD50 Workshop (CERN)

Sensors with intrinsic gain

CERN, 6/2-024 - BE Auditorium Meyrin
6-2-024

Thu, December 3

9:00 AM

Sensors with intrinsic gain

Session | **Location:** CERN, 6/2-024 - BE Auditorium Meyrin, 6-2-024

09:00 - 09:20 **IV-characterization of silicon sensors irradiated up to $2E16 \text{ neq/cm}^2$**

Speaker

Sven Wonsak

09:20 - 09:40

The effective bandgap and current related damage rate of highly irradiated silicon sensors

Speaker

Moritz Wiehe

09:40 - 10:00

Drift Mobility and Electric Field in Silicon Detectors Irradiated with Neutrons and Protons up to $1E17 \text{ n}_{\text{eq}}/\text{cm}^2$ [Thu/Friday]

Speaker

Marko Mikuz

10:00 - 10:20

Analysis of TCT measurements of highly irradiated silicon pad diodes under forward bias

Speaker

Christian Scharf

10:20 - 10:40

Tests of the Signal from Minimum Ionising Particles of $50\mu\text{m}$ Thick Silicon Micro-Strip Sensors after Extreme Fluences above $3E16 \text{ Neq cm}^2$

Speaker

Gianluigi Casse

10:40 - 11:00

Discussion Session on High Fluence Effects/Radiation

Speaker

Eckhart Fretwurst

11:00 - 11:20

Coffee break

11:20 - 11:50

Status of CNM developments on LGAD and iLGAD detectors

Speaker

Dr Salvador Hidalgo

11:50 - 12:00

Characterization of LGAD sensors from CNM Run 7062

Speaker

Isidro Mateu Suau

12:00 - 12:20

Characterization of LGAD sensors from CNM Run 7859

Speaker
Sofia Otero Ugobono

12:20 - 12:40 **Negative feedback in Si detectors with avalanche multiplication**

Speaker
Dr Vladimir Eremin

12:40 - 13:00

Timing resolution of 300-micron thick LGAD sensors from CNM at testbeam and comparison with simulation.

Speaker
Nicolo Cartiglia

13:00 - 13:20 **Reading out thin LGADs**

Speaker
Hartmut Sadrozinski

1:20 PM